

# METHOD FOR MANUFACTURING DEVICE SUBSTRATE WITH METAL BACK-GATE AND STRUCTURE FORMED THEREBY

## **ABSTRACT OF THE DISCLOSURE**

A method (and resultant structure) of forming a semiconductor device, includes forming a metal-back-gate over a substrate and a metal back-gate, forming a passivation layer on the metal back-gate to prevent the metal back-gate from reacting with radical species, and providing an intermediate gluing layer between the substrate and the metal back-gate to enhance adhesion.